Jang-Yeon Kwon

List of Publications by Year in descending order

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42 papers

1,540 citations

393982 19 h-index 315357 38 g-index

42 all docs 42 docs citations

times ranked

42

2263 citing authors

#	Article	IF	CITATIONS
1	Vacuum-free solution-based metallization (VSM) of a-IGZO using trimethylaluminium solution. RSC Advances, 2022, 12, 3518-3523.	1.7	5
2	High mobility silicon indium oxide thin-film transistor fabrication by sputtering process. Vacuum, 2022, 199, 110963.	1.6	8
3	Humidity-induced synaptic plasticity of ZnO artificial synapses using peptide insulator for neuromorphic computing. Journal of Materials Science and Technology, 2022, 119, 150-155.	5.6	11
4	Fully Degradable Memristors and Humidity Sensors Based on a Tyrosine-Rich Peptide. ACS Applied Electronic Materials, 2021, 3, 3372-3378.	2.0	14
5	Encapsulation-enhanced switching stability of MoS2 memristors. Journal of Alloys and Compounds, 2021, 885, 161016.	2.8	12
6	Synaptic transistors based on a tyrosine-rich peptide for neuromorphic computing. RSC Advances, 2021, 11, 39619-39624.	1.7	2
7	Proton-enabled activation of peptide materials for biological bimodal memory. Nature Communications, 2020, 11, 5896.	5.8	36
8	Tyrosineâ€Rich Peptide Insulator for Rapidly Dissolving Transient Electronics. Advanced Materials Technologies, 2020, 5, 2000516.	3.0	7
9	Energy scavenging artificial nervous system for detecting rotational movement. Nano Energy, 2020, 74, 104912.	8.2	29
10	Evaluation of Metal Oxide Thin-Film Electrolyte-Gated Field Effect Transistors for Glucose Monitoring in Small Volume of Body Analytes. IEEE Sensors Journal, 2020, , 1-1.	2.4	10
11	Quantitative analysis of the coupling between proton and electron transport in peptide/manganese oxide hybrid films. Physical Chemistry Chemical Physics, 2020, 22, 7537-7545.	1.3	8
12	Light-induced bias stability of crystalline indium-tin-zinc-oxide thin film transistors. Applied Surface Science, 2020, 526, 146655.	3.1	17
13	Effective surface diffusion of nickel on single crystal \hat{l}^2 -Ga ₂ O ₃ for Schottky barrier modulation and high thermal stability. Journal of Materials Chemistry C, 2019, 7, 10953-10960.	2.7	26
14	Hexagonal Boron Nitride for Surface Passivation of Two-Dimensional van der Waals Heterojunction Solar Cells. ACS Applied Materials & Solar Cells. ACS	4.0	42
15	Enhanced Device Stability of Ionic Gating Molybdenum Disulfide Transistors. Physica Status Solidi - Rapid Research Letters, 2019, 13, 1900142.	1.2	3
16	Thermo and flex multi-functional array ionic sensor for a human adaptive device. RSC Advances, 2019, 9, 36960-36966.	1.7	2
17	Highly Reliable Amorphous In-Ga-Zn-O Thin-Film Transistors Through the Addition of Nitrogen Doping. IEEE Transactions on Electron Devices, 2019, 66, 457-463.	1.6	24
18	Effects of proton conduction on dielectric properties of peptides. RSC Advances, 2018, 8, 34047-34055.	1.7	9

#	Article	IF	Citations
19	Two-Dimensional WSe ₂ /MoS ₂ p–n Heterojunction-Based Transparent Photovoltaic Cell and Its Performance Enhancement by Fluoropolymer Passivation. ACS Applied Materials & Diterraces, 2018, 10, 35972-35977.	4.0	51
20	Physically Transient Field-Effect Transistors Based on Black Phosphorus. ACS Applied Materials & Samp; Interfaces, 2018, 10, 42630-42636.	4.0	22
21	Ultrasensitive, Low-Power Oxide Transistor-Based Mechanotransducer with Microstructured, Deformable Ionic Dielectrics. ACS Applied Materials & Samp; Interfaces, 2018, 10, 31472-31479.	4.0	34
22	A self-powered triboelectric microfluidic system for liquid sensing. Journal of Materials Chemistry A, 2018, 6, 14069-14076.	5.2	45
23	A Selfâ€Powered Smart Rollerâ€Bearing Based on a Triboelectric Nanogenerator for Measurement of Rotation Movement. Advanced Materials Technologies, 2018, 3, 1800219.	3.0	24
24	Polydopamine–Copper Hybrid Films as Source and Drain for Oxide Semiconductor Fieldâ€Effect Transistors. Advanced Electronic Materials, 2018, 4, 1800046.	2.6	1
25	Enzyme immobilization on metal oxide semiconductors exploiting amine functionalized layer. RSC Advances, 2017, 7, 19656-19661.	1.7	18
26	Impact of bias stability for crystalline InZnO thin-film transistors. Applied Physics Letters, 2017, 110, .	1.5	22
27	A transparent solar cell based on a mechanically exfoliated GaTe and InGaZnO p–n heterojunction. Journal of Materials Chemistry C, 2017, 5, 4327-4334.	2.7	13
28	Increased electrical conductivity of peptides through annealing process. APL Materials, 2017, 5, .	2.2	9
29	Proton Conduction in a Tyrosineâ€Rich Peptide/Manganese Oxide Hybrid Nanofilm. Advanced Functional Materials, 2017, 27, 1702185.	7.8	23
30	A high-performance complementary inverter based on transition metal dichalcogenide field-effect transistors. Nanoscale Research Letters, 2015, 10, 115.	3.1	62
31	Reliability of Crystalline Indium–Gallium–Zinc-Oxide Thin-Film Transistors Under Bias Stress With Light Illumination. IEEE Transactions on Electron Devices, 2015, 62, 2900-2905.	1.6	32
32	Electrical stability of multilayer MoS2 field-effect transistor under negative bias stress at various temperatures. Physica Status Solidi - Rapid Research Letters, 2014, 8, 714-718.	1.2	42
33	Self-Limiting Film Growth of Transparent Conducting In ₂ O ₃ by Atomic Layer Deposition using Trimethylindium and Water Vapor. Journal of Physical Chemistry C, 2011, 115, 15384-15389.	1.5	66
34	Review paper: Transparent amorphous oxide semiconductor thin film transistor. Electronic Materials Letters, 2011, 7, 1-11.	1.0	253
35	Structural and Electrical Properties of Atomic Layer Deposited Alâ€Doped ZnO Films. Advanced Functional Materials, 2011, 21, 448-455.	7.8	233
36	Reliability of Oxide Thin Film Transistors under the Gate Bias Stress with 400 nm Wavelength Light Illumination. Materials Research Society Symposia Proceedings, 2011, 1321, 253.	0.1	0

#	Article	lF	CITATIONS
37	Ti/Cu bilayer electrodes for SiNx-passivated Hf–In–Zn–O thin film transistors: Device performance and contact resistance. Applied Physics Letters, 2010, 97, 162105.	1.5	27
38	The effect of moisture on the photon-enhanced negative bias thermal instability in Ga–In–Zn–O thin film transistors. Applied Physics Letters, 2009, 95, .	1.5	289
39	The Simulation of Copper Drift in SiO2 during Bias Temperature Stress (BTS) Test. Materials Research Society Symposia Proceedings, 2002, 731, 8171.	0.1	O
40	Solid Phase Crystallization (SPC) Behavior of Amorphous Si Bilayer Films with Different Concentration of Oxygen: <i>Surface vs. Interface-nucleation</i> Symposia Proceedings, 2000, 621, 631.	0.1	7
41	Si/sub 0.7/Ge/sub 0.3/ Quantum Dot Formation by Interface Agglomeration. , 1998, , .		O
42	Programming dynamics of a single electron memory cell with a high-density SiGe nanocrystal array at room temperature. , 0, , .		2